Single, Dual, and Quad Micropower, Zero-Drift, RRIO Operational Amplifiers

The ISL28133, ISL28233 are single and dual micropower, zero-drift operational amplifiers that are optimized for single supply operation from 1.65V to 5.5V. Their low supply current of 18µA and wide input range enable the ISL28133 to be an excellent general purpose op amp for a range of applications. The ISL28133 is ideal for handheld devices that operates off 2 AA or single Li-ion batteries.

The ISL28133 is available in the 5 Ld SOT-23, the 5 Ld SC70 and the 6 Ld 1.6mmx1.6mm µTDFN packages. All devices operates over the extended temperature range of -40°C to +125°C.

Ordering Information

PART NUMBER	PART MARKING	PACKAGE (Pb-Free)	PKG. DWG. #
ISL28133FHZ-T7* (Note 1)	BCFA	5 Ld SOT-23	MDP0038
Coming Soon ISL28133FHZ-T7A* (Note 1)	BCFA	5 Ld SOT-23	MDP0038
Coming Soon ISL28133FEZ-T7* (Note 1)	BHA	5 Ld SC70	P5.049
Coming Soon ISL28133FEZ-T7A* (Note 1)	BHA	5 Ld SC70	P5.049
Coming Soon ISL28133FRUZ-T7* (Note 2)	T8	6 Ld µTDFN	L6.1.6x1.6
Coming Soon ISL28233FUZ (Note 1)	8233Z	8 Ld MSOP	MDP0043
Coming Soon ISL28233FUZ-T7* (Note 1)	8233Z	8 Ld MSOP	MDP0043
Coming Soon ISL28233FRTZ-T7* (Note 1)	TBD	8 Ld TDFN	TBD
Coming Soon ISL28433FVZ (Note 1)	TBD	14 Ld TSSOP	M14.173

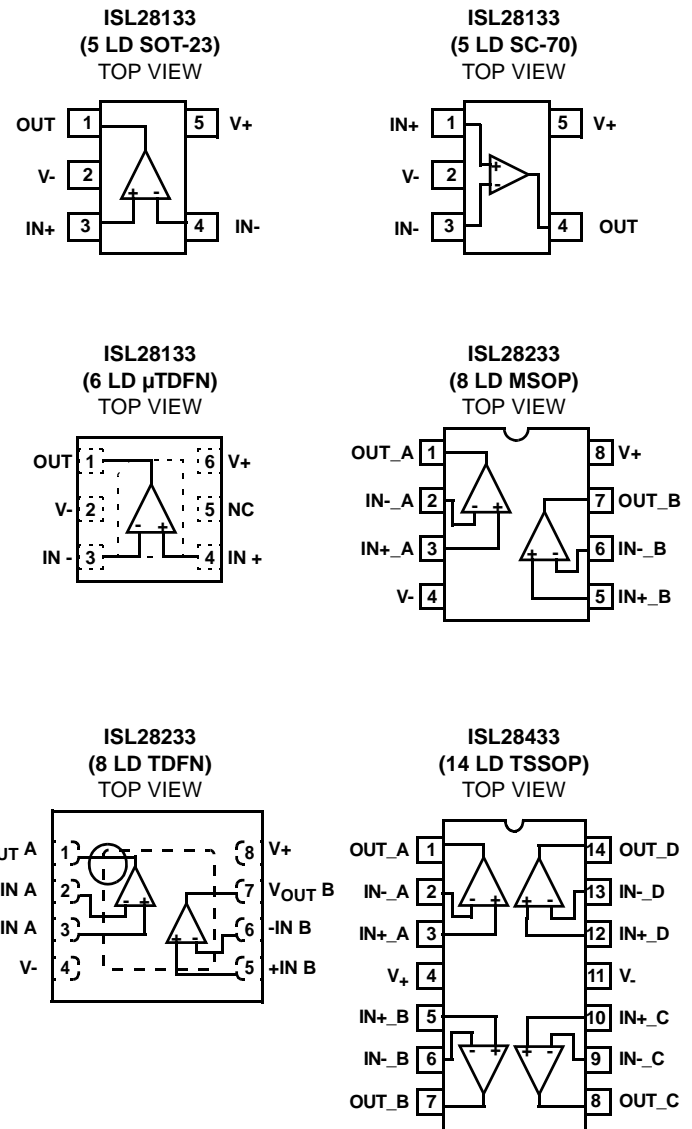*Please refer to TB347 for details on reel specifications.
NOTES:

1. These Intersil Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

2. These Intersil Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and NiPdAu plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Features

- Low Input Offset Voltage . . . . 8µV, Max.

- Low Offset Drift. . . . . 0.075µV/°C, Max

- Quiescent Current . . . . 18µA, Typ.

- Wide Supply Range . . . . 1.65V to 5.5V

- Low Noise (0.01Hz to 10Hz). . . . . 1.1µV$_{P-P}$, Typ.

- Rail-to-Rail Inputs and Output

- Input Bias Current . . . . 300pA, Max.

- Operating Temperature Range. . . . . -40°C to +125°C

Pinouts

ISL28133 (5 LD SOT-23) TOP VIEW

ISL28133 (5 LD SC-70) TOP VIEW

ISL28133 (6 LD µTDFN) TOP VIEW

ISL28233 (8 LD MSOP) TOP VIEW

ISL28233 (8 LD TDFN) TOP VIEW

ISL28433 (14 LD TSSOP) TOP VIEW

Absolute Maximum Ratings

Max Supply Voltage V+ to V- 5.75V
Max Voltage VIN to GND . . . . -0.5V to 5.75V
Max Input Differential Voltage 5.75V
Max Input Current 20mA
Max Voltage VOUT to GND (10s) 5.75V
ESD Rating
  Human Body Model 3000V
  Machine Model. 200V
  Charged Device Model. 1500V

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)
5 Ld SOT-23.	225
5 Ld SC70	206
6 Ld µTDFN	240

Maximum Storage Temperature Range. . . . .-65°C to +150°C
Pb-Free Reflow Profile. . . . . .see link below
  http://www.intersil.com/pbfree/Pb-FreeReflow.asp

Operating Conditions

Temperature Range . . . .-40°C to +125°C

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTE:

3. θ_{JA} is measured with the component mounted on a high effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

Electrical Specifications

V_+ = 5V, V_- = 0V, VCM = 2.5V, T_A = +25°C, R_L = 10kΩ, unless otherwise specified. **Boldface limits apply over the operating temperature range, -40°C to +125°C.**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 4)	TYP	MAX (Note 4)	UNIT
DC SPECIFICATIONS						
V_{OS}	Input Offset Voltage		-8	±2	8	µV
			-15.5		**15.5**	µV
TCV_{OS}	Input Offset Voltage Temperature Coefficient			**0.02**	**0.075**	µV/°C
I_{OS}	Input Offset Current			-60		pA
I_B	Input Bias Current		-300	±30	300	pA
			-600		**600**	pA
Common Mode Input Voltage Range		V+ = 5.0V, V- = GND	-0.1		5.1	V
CMRR	Common Mode Rejection Ratio	VCM = -0.1V to 5.0V	118	125		dB
			115			dB
PSRR	Power Supply Rejection Ratio	Vs = 2V to 5.5V	110	138		dB
			110			dB
V_{OH}	Output Voltage Swing, High	R_L = 10kΩ	**4.965**	4.981		V
V_{OL}	Output Voltage Swing, Low			18	**35**	mV
A_{OL}	Open Loop Gain	R_L = 1MΩ		200		dB
V_+	Supply Voltage	**(Note 5)**	1.65		5.5	V
I_S	Supply Current	R_L = OPEN		18	25	µA
					35	µA
I_{SC+}	Output Source Short Circuit Current	R_L = Short to ground or V+	13	17	26	mA
I_{SC-}	Output Sink Short Circuit Current		-26	-19	-13	mA
AC SPECIFICATONS						
GBWP	Gain Bandwidth Product f = 50kHz	A_V = 100, R_F = 100kΩ, R_G = 1kΩ, R_L = 10kΩ to V_{CM}		400		kHz
$e_N V_{P-P}$	Peak-to-Peak Input Noise Voltage	f = 0.01Hz to 10Hz		1.1		µV$_{P-P}$
e_N	Input Noise Voltage Density	f = 1kHz		65		nV/√(Hz)

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Electrical Specifications   V$_+$ = 5V, V$_-$ = 0V, VCM = 2.5V, T$_A$ = +25°C, R$_L$ = 10kΩ, unless otherwise specified. **Boldface limits apply over the operating temperature range, -40°C to +125°C. (Continued)**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 4)	TYP	MAX (Note 4)	UNIT
i$_N$	Input Noise Current Density	f = 1kHz		72		fA/√(Hz)
		f = 10Hz		79		fA/√(Hz)
C$_{in}$	Differential Input Capacitance	f = 1MHz		1.6		pF
	Common Mode Input Capacitance			1.12		pF
TRANSIENT RESPONSE						
SR	Positive Slew Rate	V$_{OUT}$ = 1V to 4V, R$_L$ = 10kΩ		0.2		V/µs
	Negative Slew Rate			0.1		V/µs
t$_r$, t$_f$, Small Signal	Rise Time, t$_r$ 10% to 90%	A$_V$ = +1, V$_{OUT}$ = 0.1V$_{P-P}$, R$_F$ = 0Ω, R$_L$ = 10kΩ, C$_L$ = 1.2pF		1.1		µs
	Fall Time, t$_f$ 10% to 90%			1.1		µs
t$_r$, t$_f$ Large Signal	Rise Time, t$_r$ 10% to 90%	A$_V$ = +1, V$_{OUT}$ = 2V$_{P-P}$, R$_F$ = 0Ω, R$_L$ = 10kΩ, C$_L$ = 1.2pF		8		µs
	Fall Time, t$_f$ 10% to 90%			10		µs
t$_s$	Settling Time to 0.1%, 2V$_{P-P}$ Step	A$_V$ = +1, R$_F$ = 0Ω, R$_L$ = 10kΩ, C$_L$ = 1.2pF		35		µs

NOTES:

4. Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

5. Parts are 100% tested with a minimum operating voltage of 1.65V to a VOS limit of ±15µV.

Typical Performance Curves   V+ = 5V, V- = 0V, V$_{CM}$ = 2.5V, R$_L$ = Open.
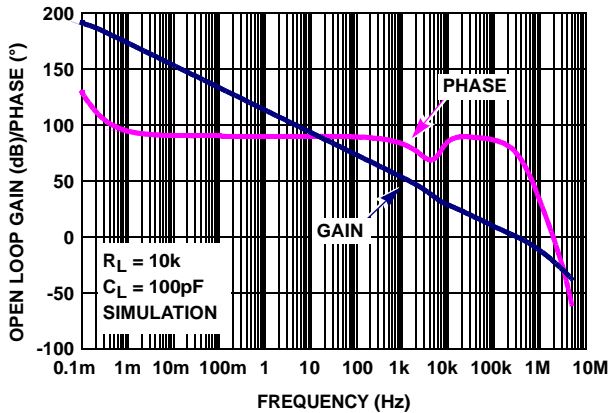
FIGURE 1. FREQUENCY RESPONSE vs OPEN LOOP GAIN, R$_L$ = 10k
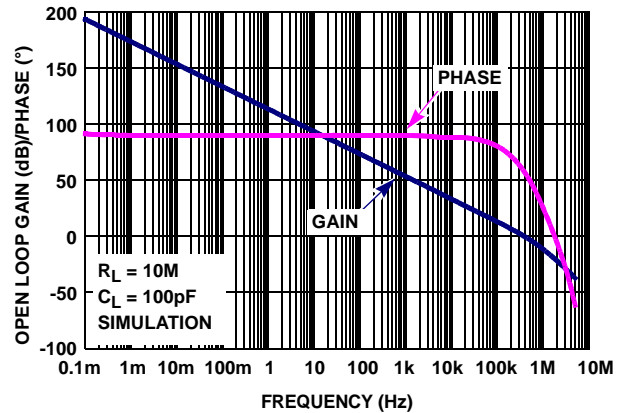
FIGURE 2. FREQUENCY RESPONSE vs OPEN LOOP GAIN, R$_L$ = 10M

Typical Performance Curves V+ = 5V, V- = 0V, V$_{CM}$ = 2.5V, R$_L$ = Open. **(Continued)**
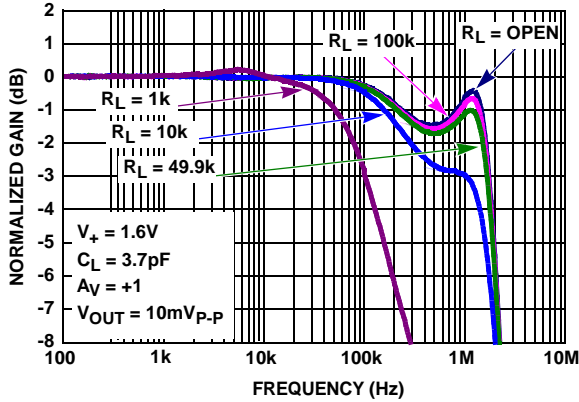
FIGURE 3. GAIN vs FREQUENCY vs R$_L$, V$_S$ = 1.6V
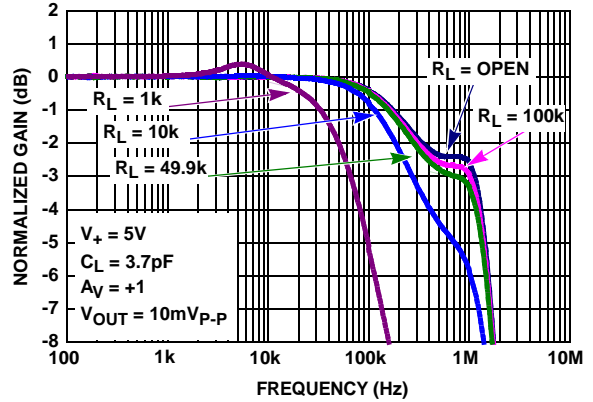
FIGURE 4. GAIN vs FREQUENCY vs R$_L$, V$_S$ = 5V
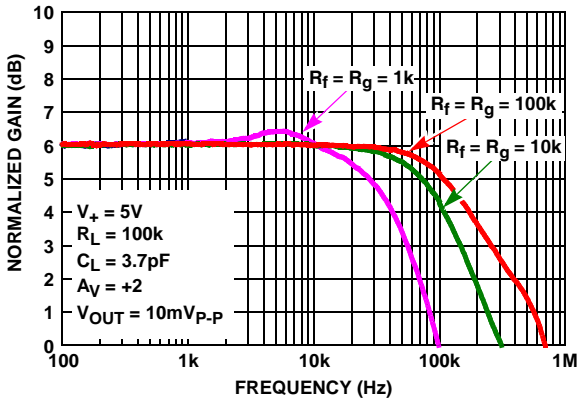
FIGURE 5. GAIN vs FREQUENCY vs FEEDBACK RESISTOR VALUES R$_f$/R$_g$
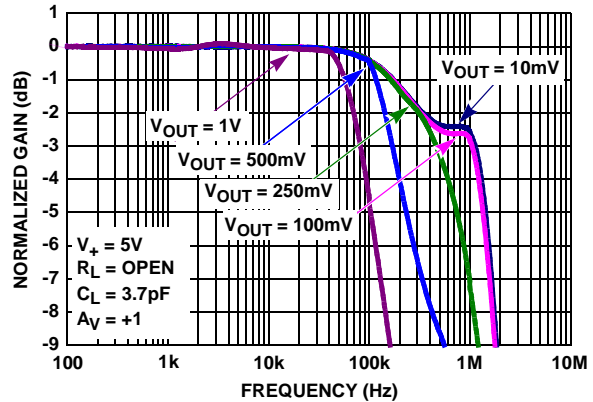
FIGURE 6. GAIN vs FREQUENCY vs V$_{OUT}$, R$_L$ = OPEN
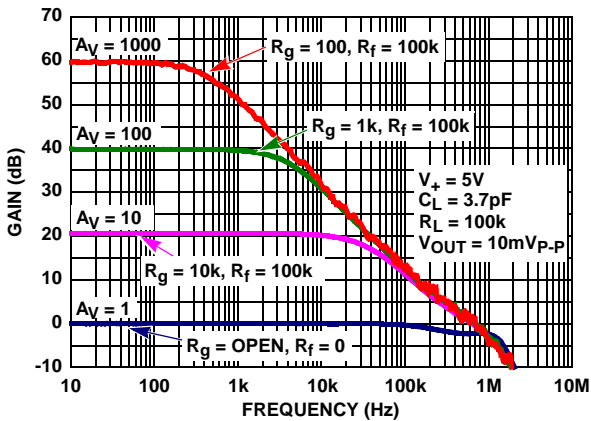
FIGURE 7. FREQUENCY RESPONSE vs CLOSED LOOP GAIN
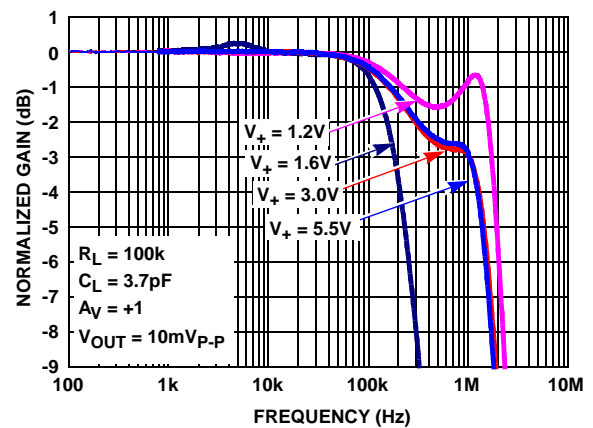
FIGURE 8. GAIN vs FREQUENCY vs SUPPLY VOLTAGE

Typical Performance Curves V+ = 5V, V- = 0V, V$_{CM}$ = 2.5V, R$_L$ = Open. **(Continued)**
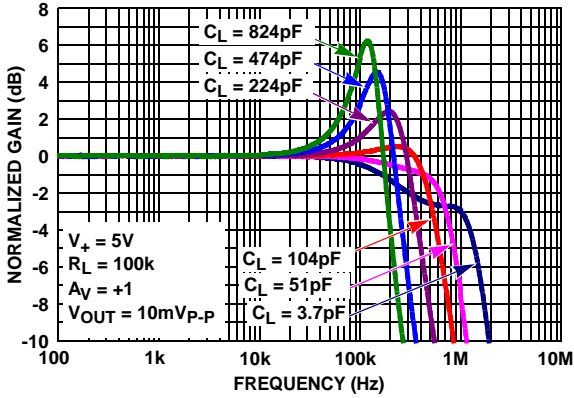
FIGURE 9. GAIN vs FREQUENCY vs C$_L$
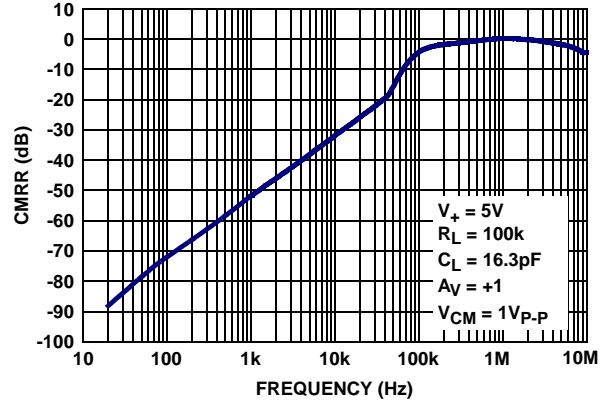
FIGURE 10. CMRR vs FREQUENCY, V$_S$ = 5V
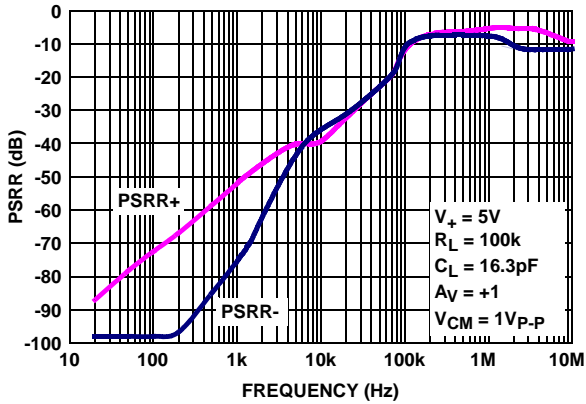
FIGURE 11. PSRR vs FREQUENCY, V$_S$ = 5V
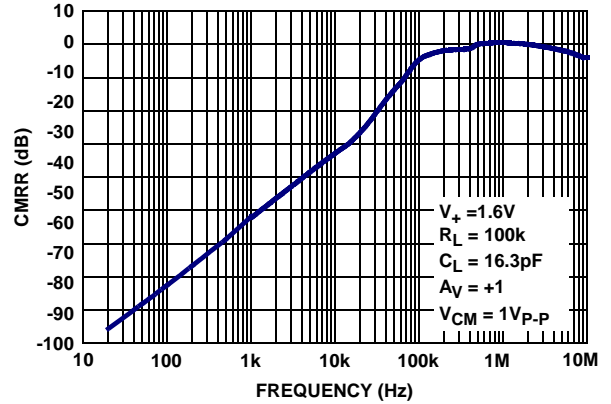
FIGURE 12. CMRR vs FREQUENCY, V$_S$ = 1.6V
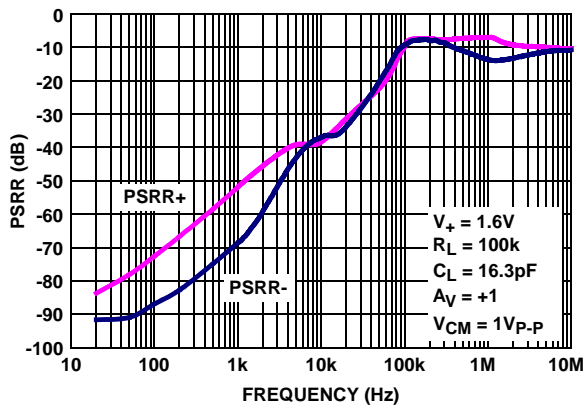
FIGURE 13. PSRR vs FREQUENCY, V$_S$ = 1.6V
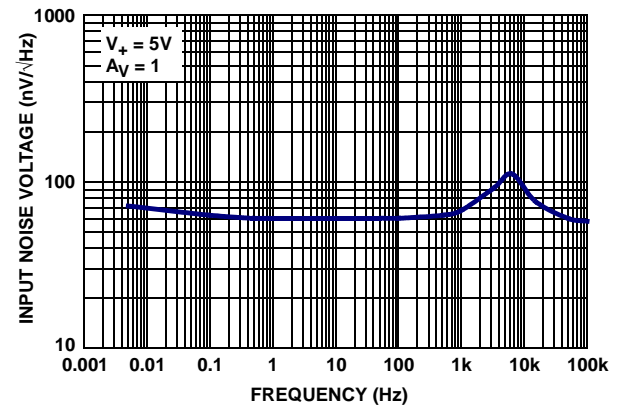
FIGURE 14. INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

Typical Performance Curves V+ = 5V, V- = 0V, V$_{CM}$ = 2.5V, R$_L$ = Open. **(Continued)**
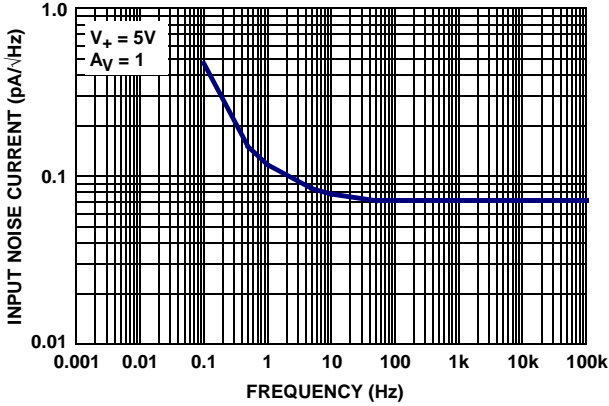
FIGURE 15. INPUT NOISE CURRENT DENSITY vs FREQUENCY
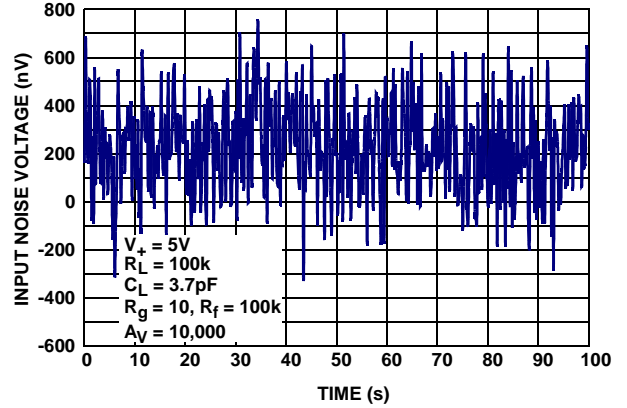
FIGURE 16. INPUT NOISE VOLTAGE 0.1Hz TO 10Hz
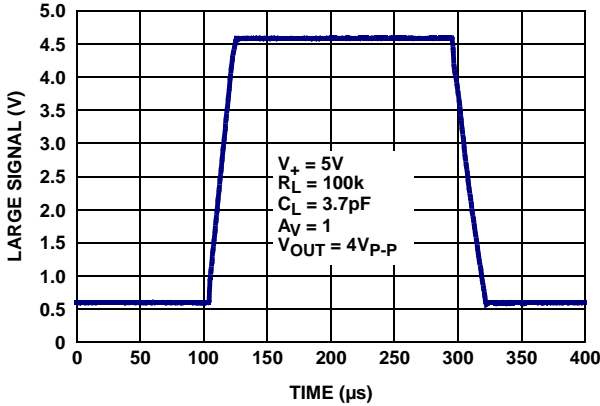
FIGURE 17. LARGE SIGNAL STEP RESPONSE (4V)
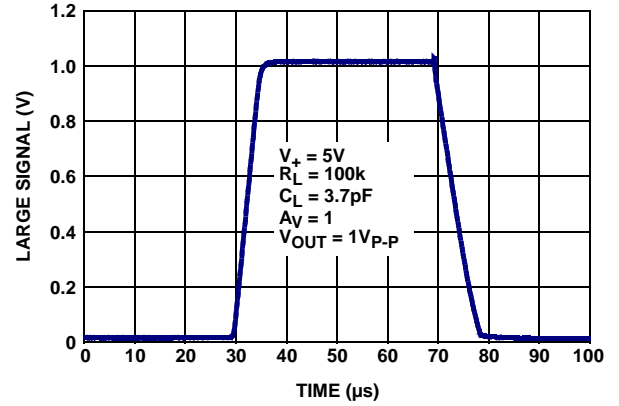
FIGURE 18. LARGE SIGNAL STEP RESPONSE (1V)
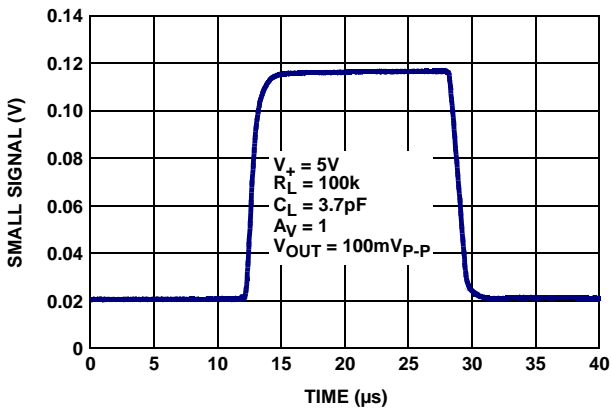
FIGURE 19. SMALL SIGNAL STEP RESPONSE (100mV)
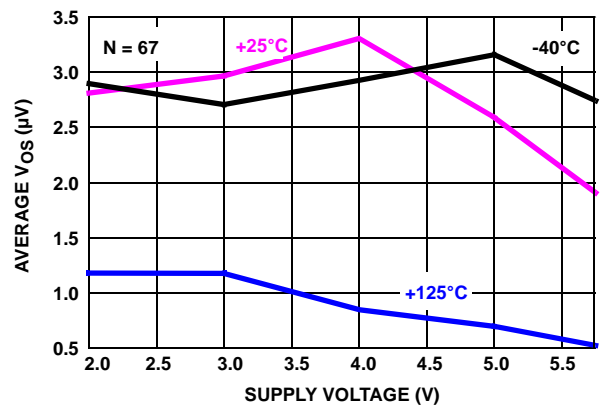
FIGURE 20. AVERAGE INPUT OFFSET VOLTAGE vs SUPPLY VOLTAGE

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Typical Performance Curves   V+ = 5V, V- = 0V, V_CM = 2.5V, R_L = Open. **(Continued)**

FIGURE 21. V_OS vs TEMPERATURE, V_S = ±1.0V, V_IN = 0V, R_L = INF
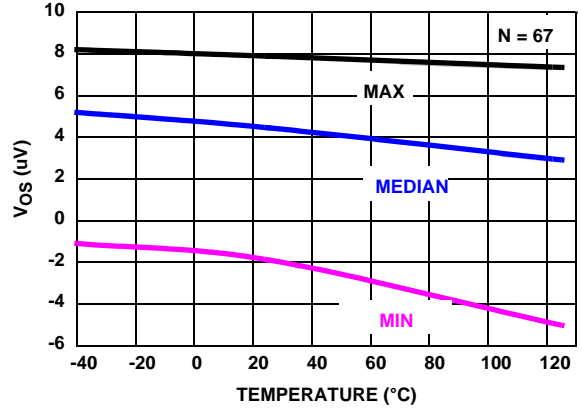
FIGURE 22. V_OS vs TEMPERATURE, V_S = ±2.5V, V_IN = 0V, R_L = INF
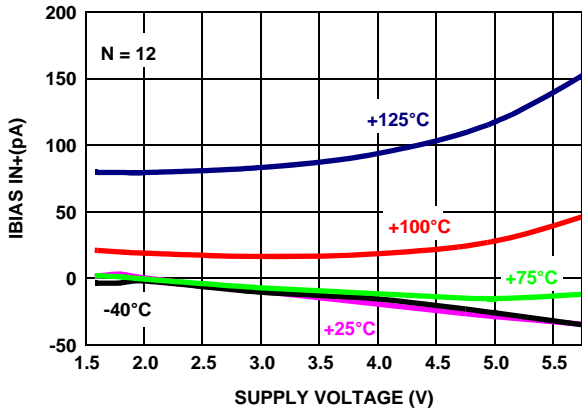
FIGURE 23. AVERAGE NON-INVERTING INPUT BIAS CURRENT vs SUPPLY VOLTAGE vs TEMPERATURE
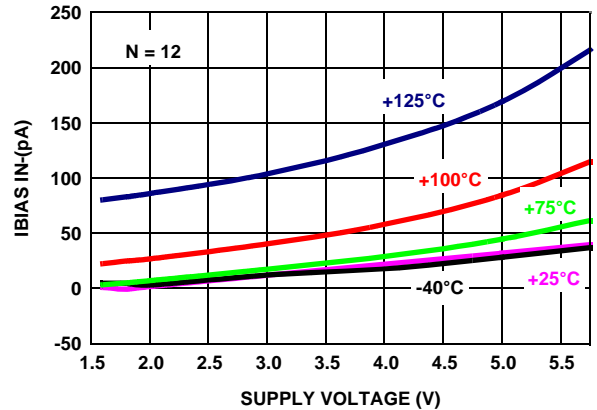
FIGURE 24. AVERAGE INVERTING INPUT BIAS CURRENT vs SUPPLY VOLTAGE vs TEMPERATURE
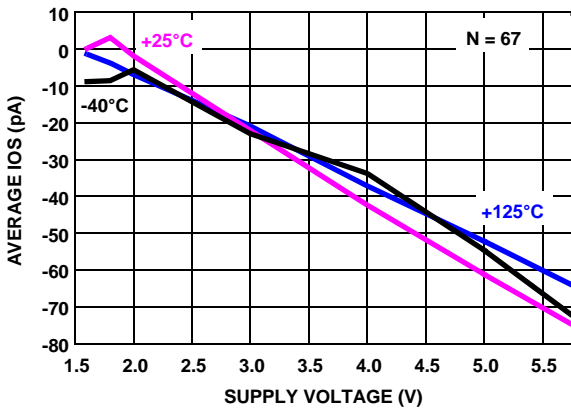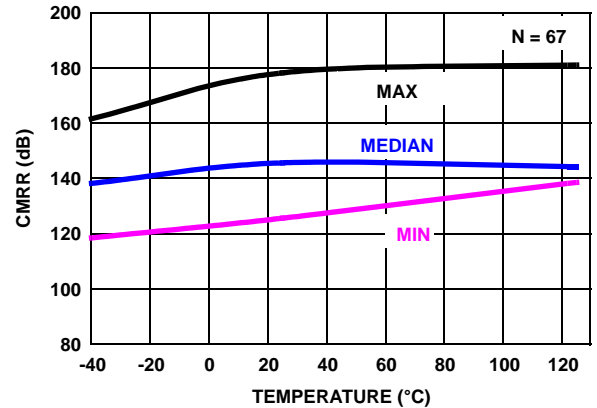

FIGURE 25. IOS vs SUPPLY VOLTAGE vs TEMPERATURE

FIGURE 26. CMRR vs TEMPERATURE, VCM = -2.5V TO +2.5V, V+ = ±2.5V

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Typical Performance Curves V+ = 5V, V- = 0V, V_CM = 2.5V, R_L = Open. **(Continued)**
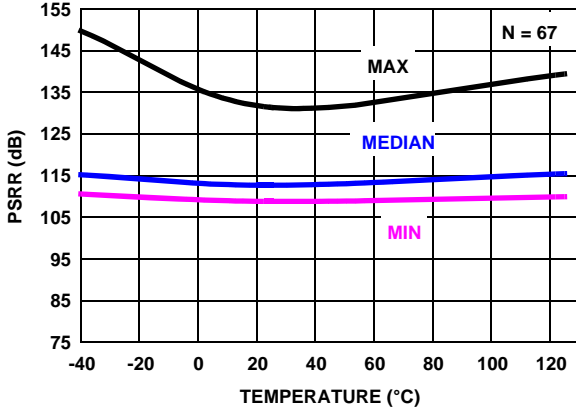

FIGURE 27. PSRR vs TEMPERATURE, V+ = 2V TO 5.5V

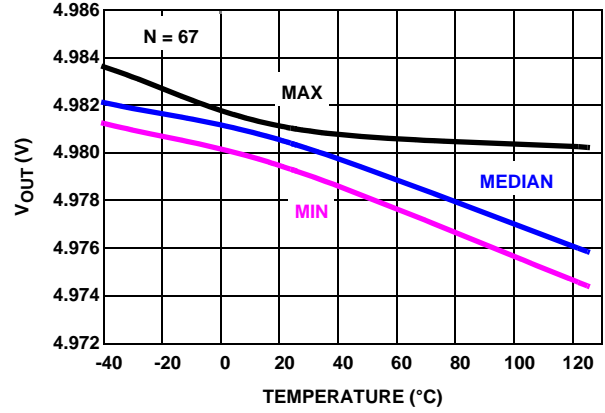FIGURE 28. V_OUT HIGH vs TEMPERATURE, R_L = 10k, V_S +-2.5V
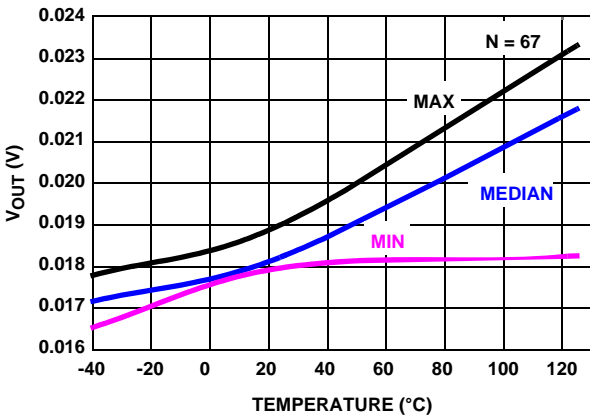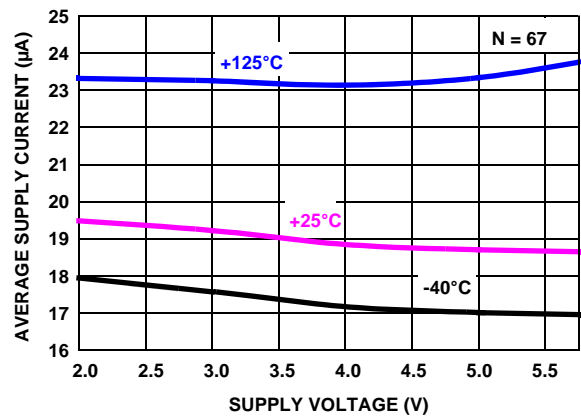

FIGURE 29. V_OUT LOW vs TEMPERATURE, R_L = 10k, V_S +-2.5V

FIGURE 30. SUPPLY CURRENT vs SUPPLY VOLTAGE
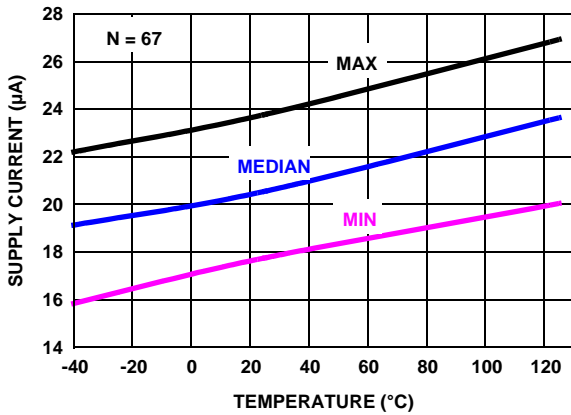

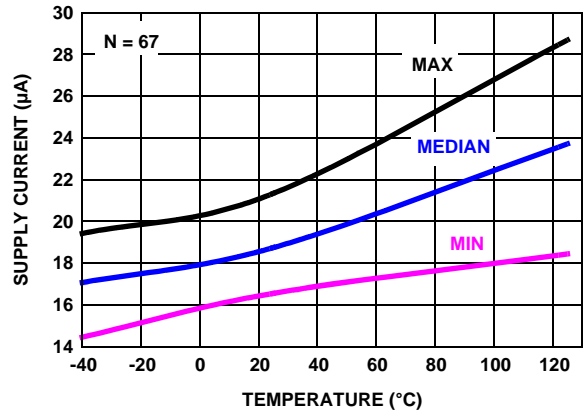FIGURE 31. V+ SUPPLY CURRENT vs TEMPERATURE,
V_S = ±0.8V, V_IN = 0V, R_L = INF

FIGURE 32. V+ SUPPLY CURRENT vs TEMPERATURE,
V_S = ±2.5V, V_IN = 0V, R_L = INF

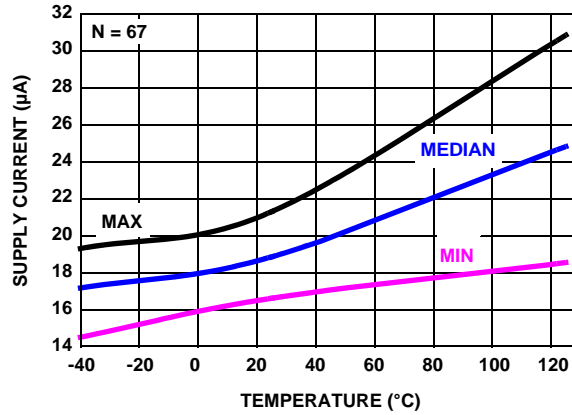## Typical Performance Curves V+ = 5V, V- = 0V, V_CM = 2.5V, R_L = Open. **(Continued)**

FIGURE 33. V+ SUPPLY CURRENT vs TEMPERATURE, V_S = ±3.0V, V_{IN} = 0V, R_L = INF

Pin Descriptions

| ISL28133 (5 Ld SOT23)	ISL28133 (5 Ld SC70)	ISL28133 (6 Ld µTDFN)	ISL28233 (8 Ld MSOP, 8 Ld TDFN)	ISL28433 (14 Ld TSSOP)	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
3	1	4	3(A) 5(B)	3(A) 5(B) 10(C) 12(D)	IN+	Non-inverting input	**Circuit 1**
2	2	2	4	11	V-	Negative supply	
4	3	3	2(A) 6(B)	2(A) 6(B) 9(C) 13(D)	IN-	Inverting input	(See Circuit 1)
1	4	1	1(A) 7(B)	1(A) 7(B) 8(C) 14(D)	OUT	Output	**Circuit 2**
5	5	6	8	4	V+	Positive supply	
		5			NC	Not connected	Not internally connected
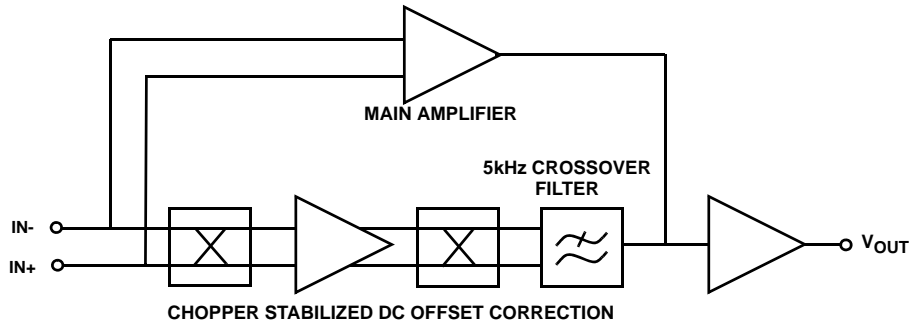
FIGURE 34. ISL28x33 FUNCTIONAL BLOCK DIAGRAM

Applications Information

Functional Description

The ISL28133 uses a proprietary auto-zero architecture (Figure 34) that combines a 400kHz main amplifier with a very high open loop gain (200dB) chopper stabilized amplifier to achieve very low offset voltage and drift (2μV, 0.02μV/°C typical) while consuming only 18μA of supply current per channel.

This multi-path amplifier architecture contains a time continuous main amplifier whose input DC offset is corrected by a parallel-connected, high gain chopper stabilized DC correction amplifier operating at 100kHz. From DC to ~5kHz, both amplifiers are active with DC offset correction and most of the low frequency gain is provided by the chopper amplifier. A 5kHz crossover filter cuts off the low frequency amplifier path leaving the main amplifier active out to the 400kHz gain-bandwidth product of the device.

The key benefits of this architecture for precision applications are very high open loop gain, very low DC offset, and low 1/f noise. The noise is virtually flat across the frequency range from a few millihertz out to 100kHz, except for the narrow noise peak at the amplifier crossover frequency (5kHz).

Rail-to-rail Input and Output (RRIO)

The RRIO CMOS amplifier uses parallel input PMOS and NMOS that enable the inputs to swing 100mV beyond either supply rail. The inverting and non-inverting inputs do not have back-to-back input clamp diodes and are capable of maintaining high input impedance at high differential input voltages. This is effective in eliminating output distortion caused by high slew-rate input signals.

The output stage uses common source connected PMOS and NMOS devices to achieve rail-to-rail output drive capability with 17mA current limit and the capability to swing to within 20mV of either rail while driving a 10kΩ load.

IN+ and IN- Protection

All input terminals have internal ESD protection diodes to both positive and negative supply rails, limiting the input voltage to within one diode beyond the supply rails. For applications

where either input is expected to exceed the rails by 0.5V, an external series resistor must be used to ensure the input currents never exceed 20mA (Figure 35).
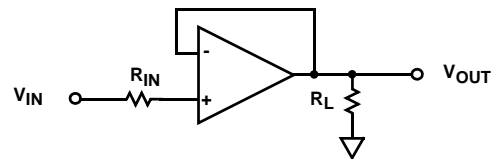

FIGURE 35. INPUT CURRENT LIMITING

Layout Guidelines for High Impedance Inputs

To achieve the maximum performance of the high input impedance and low offset voltage of the ISL28X33 amplifiers, care should be taken in the circuit board layout. The PC board surface must remain clean and free of moisture to avoid leakage currents between adjacent traces. Surface coating of the circuit board will reduce surface moisture and provide a humidity barrier, reducing parasitic resistance on the board. The use of guard rings around the amplifier inputs will further reduce leakage currents. Figure 36 shows how the guard ring should be configured. The guard ring does not need to be a specific width, but it should form a continuous loop around both inputs. By setting the guard ring voltage equal to the voltage at the non-inverting input, parasitic capacitance is minimized as well.
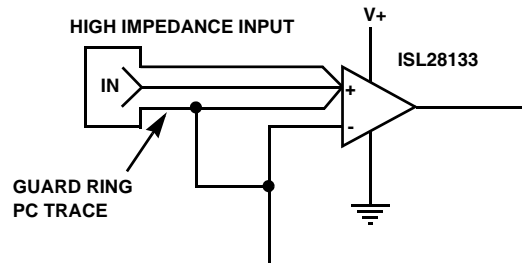

FIGURE 36. USE OF GUARD RINGS TO REDUCE LEAKAGE

High Gain, Precision DC Coupled Amplifier

The circuit in Figure 37 implements a single-stage DC coupled amplifier with an input DC sensitivity of under 100nV that is only possible using a low VOS amplifier with high open loop gain. High gain DC amplifiers operating from low

voltage supplies are not practical using typical low offset precision op amps. For example, the typical ±100µV V_{OS} and offset drift 0.5µV/°C of a low offset op amp would produce a DC error of >1V with an additional 5mV°C of temperature dependent error making it difficult to resolve DC input voltage changes in the micro-volt range.

The ±8µV max V_{OS} and 0.075µV/°C of the ISL28133 produces a temperature stable maximum DC output error of only ±80mV with a maximum temperature drift of 0.75µV/°C. The additional benefit of a very low 1/f noise corner frequency and some feedback filtering enables DC voltages and voltage fluctuations well below 100nV to be easily detected with a simple single stage amplifier.
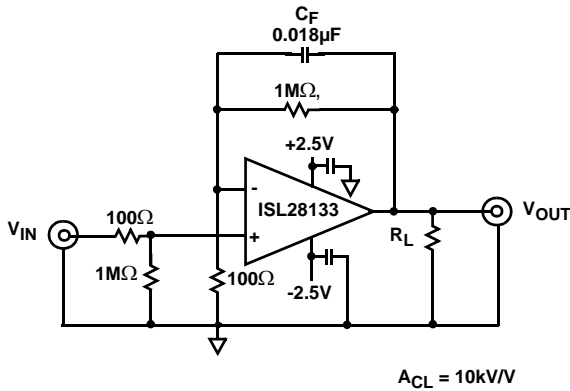

FIGURE 37. HIGH GAIN, PRECISION DC COUPLED AMPLIFIER

ISL28133 SPICE Model

Figure 38 shows the SPICE model schematic and Figure 39 shows the net list for the ISL28133 SPICE model. The model is a simplified version of the actual device and simulates important parameters such as noise, **Slew Rate,** Gain and Phase. The model uses typical parameters from the ISL28133. The poles and zeros in the model were determined from the actual open and closed-loop gain and phase response. This enables the model to present an accurate AC representation of the actual device. The model is configured for ambient temperature of +25°C.

Figures 40 through 47 show the characterization vs simulation results for the Noise Density, Frequency Response vs Close Loop Gain, Gain vs Frequency vs CL and Large Signal Step Response (4V).
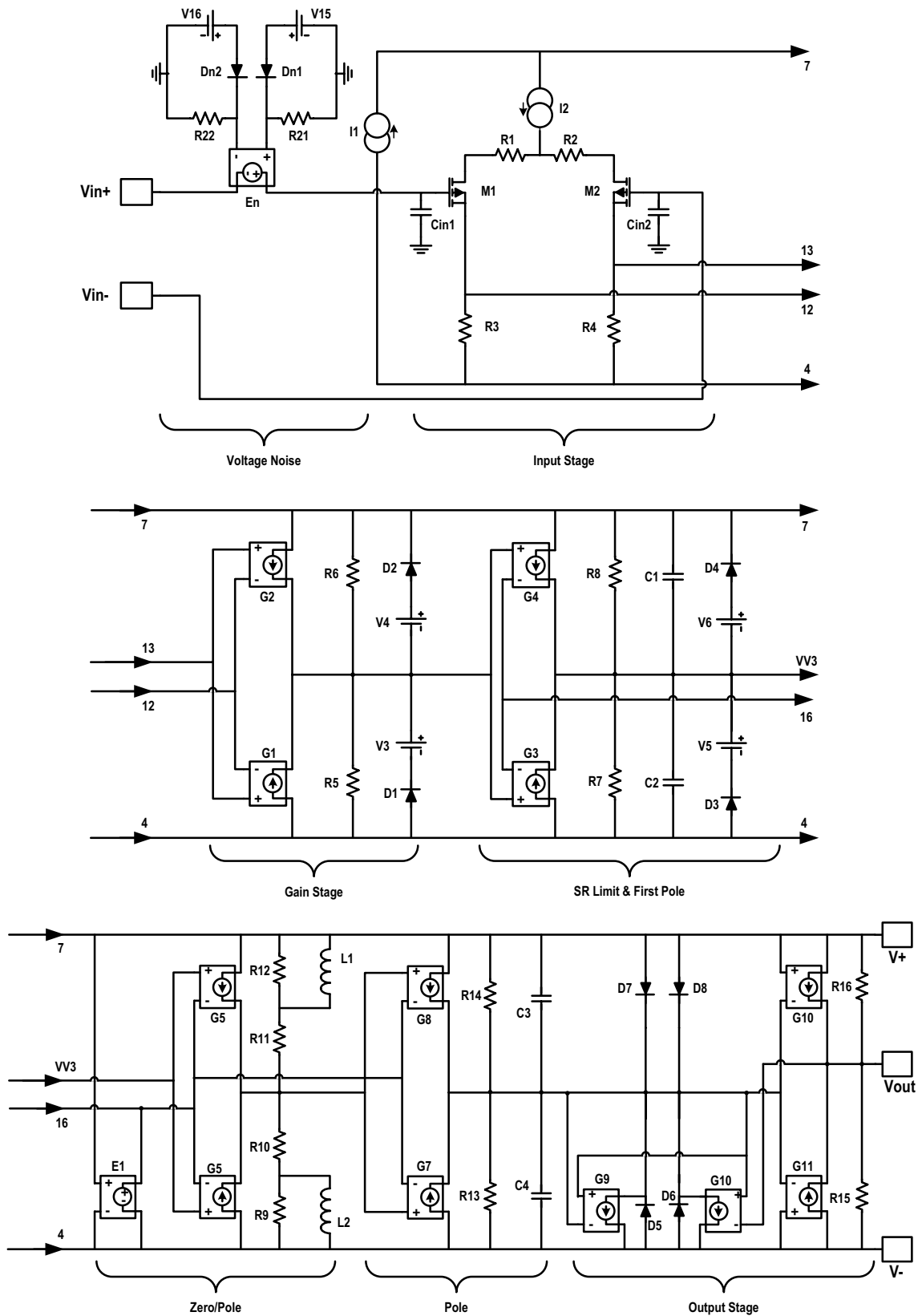
FIGURE 38. SPICE CIRCUIT SCHEMATIC

* ISL28133 Macromodel
* Revision B, April 2009
* AC characteristics, Voltage Noise
* Connections: +input
* | -input
* | | +Vsupply
* | | | -Vsupply
* | | | | output
* | | | | |
.subckt ISL28133   3   2   7   4   6
*
*Voltage Noise
D_DN1   102 101 DN
D_DN2   104 103 DN
R_R21   0 101 120k
R_R22   0 103 120k
E_EN   8 3 101 103 1
V_V15   102 0 0.1Vdc
V_V16   104 0 0.1Vdc
*
*Input Stage
C_Cin1   8 0 0.4p
C_Cin2   2 0 2.0p
R_R1   9 10 10
R_R2   10 11 10
R_R3   4 12 100
R_R4   4 13 100
M_M1   12 8 9 9   pmosisil
+ L=50u
+ W=50u
M_M2   13 2 11 11 pmosisil
+ L=50u
+ W=50u
I_I1   4 7 DC 92uA
I_I2   7 10 DC 100uA
*
*Gain stage
G_G1   4 VV2 13 12 0.0002
G_G2   7 VV2 13 12 0.0002
R_R5   4 VV2 1.3Meg
R_R6   VV2 7 1.3Meg
D_D1   4 14 DX
D_D2   15 7 DX
V_V3   VV2 14 0.7Vdc
V_V4   15 VV2 0.7Vdc
*
*SR limit first pole
G_G3   4 VV3 VV2 16 1
G_G4   7 VV3 VV2 16 1
R_R7   4 VV3 1meg
R_R8   VV3 7 1meg
C_C1   VV3 7 12u
C_C2   4 VV3 12u
D_D3   4 17 DX
D_D4   18 7 DX
V_V5   VV3 17 0.7Vdc

V_V6   18 VV3 0.7Vdc
*
*Zero/Pole
E_E1   16 4 7 4 0.5
G_G5   4 VV4 VV3 16 0.000001
G_G6   7 VV4 VV3 16 0.000001
L_L1   20 7 0.3H
R_R12   20 7 2.5meg
R_R11   VV4 20 1meg
L_L2   4 19 0.3H
R_R9   4 19 2.5meg
R_R10   19 VV4 1meg
*Pole
G_G7   4 VV5 VV4 16 0.000001
G_G8   7 VV5 VV4 16 0.000001
C_C3   VV5 7 0.12p
C_C4   4 VV5 0.12p
R_R13   4 VV5 1meg
R_R14   VV5 7 1meg
*
*Output Stage
G_G9   21 4 6 VV5 0.0000125
G_G10   22 4 VV5 6 0.0000125
D_D5   4 21 DY
D_D6   4 22 DY
D_D7   7 21 DX
D_D8   7 22 DX
R_R15   4 6 8k
R_R16   6 7 8k
G_G11   6 4 VV5 4 -0.000125
G_G12   7 6 7 VV5 -0.000125
*
.model pmosisil pmos (kp=16e-3 vto=10m)
.model DN D(KF=6.4E-16 AF=1)
.MODEL DX D(IS=1E-18 Rs=1)
.MODEL DY D(IS=1E-15 BV=50 Rs=1)
.ends ISL28133

FIGURE 39. SPICE NET LIST

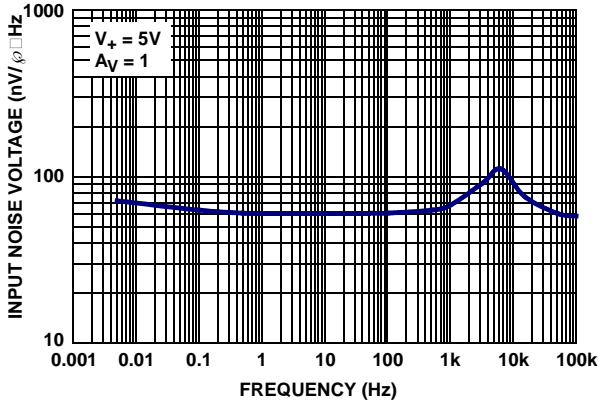## Characterization vs Simulation Results

FIGURE 40. CHARACTERIZED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY
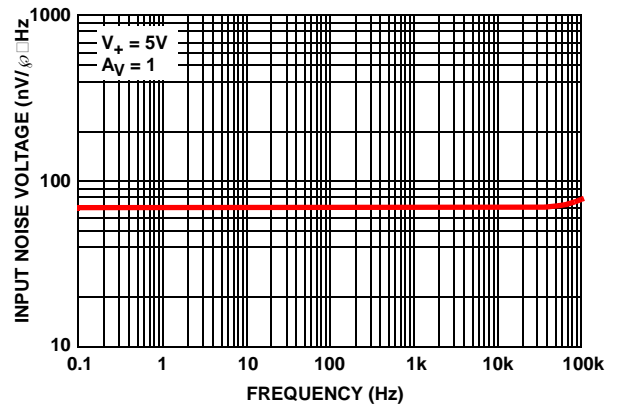

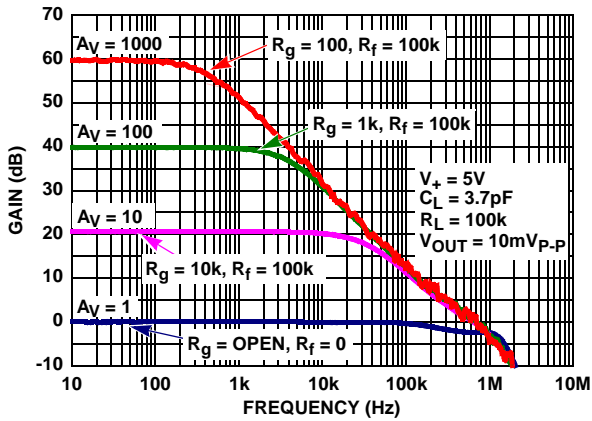FIGURE 41. SIMULATED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

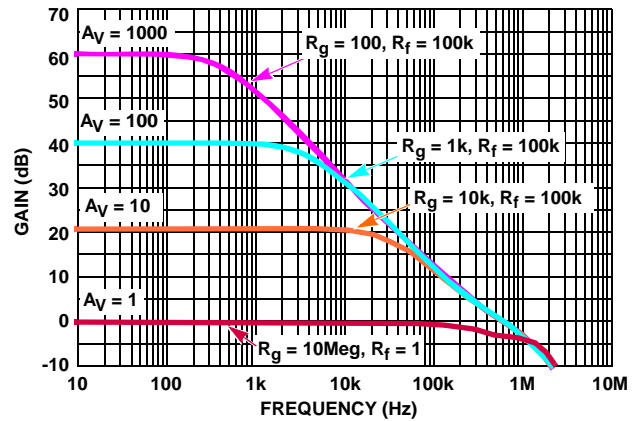FIGURE 42. CHARACTERIZED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

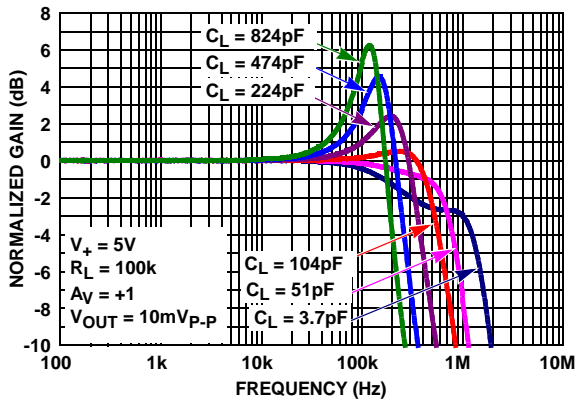FIGURE 43. SIMULATED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

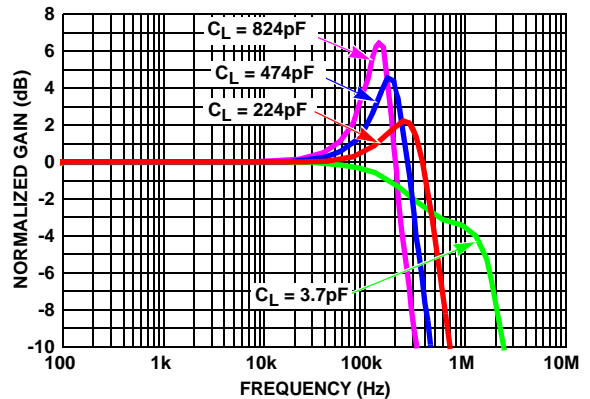FIGURE 44. CHARACTERIZED GAIN vs FREQUENCY vs C_L

FIGURE 45. SIMULATED GAIN vs FREQUENCY vs C_L
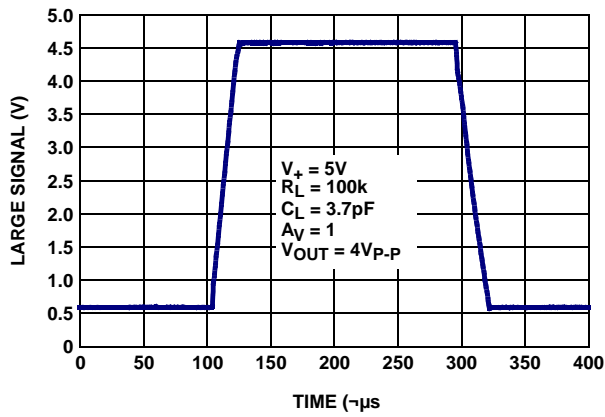
Characterization vs Simulation Results (Continued)

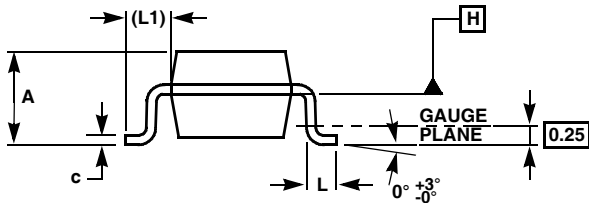
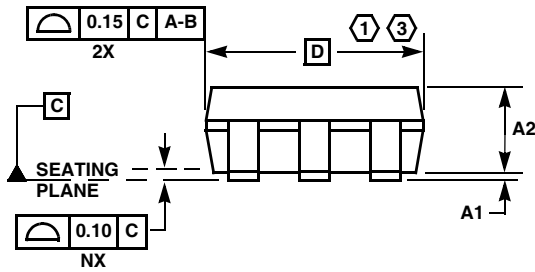FIGURE 46. CHARACTERIZED LARGE SIGNAL STEP
RESPONSE (4V)
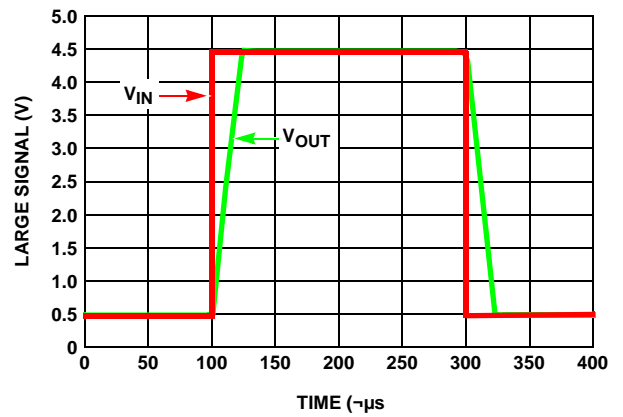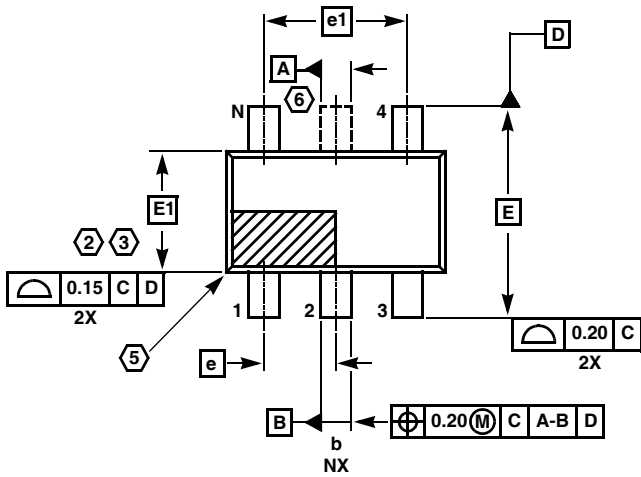

FIGURE 47. SIMULATED LARGE SIGNAL STEP RESPONSE
(4V)

SOT-23 Package Family

MDP0038
SOT-23 PACKAGE FAMILY

SYMBOL	MILLIMETERS		TOLERANCE
	SOT23-5	SOT23-6	
A	1.45	1.45	MAX
A1	0.10	0.10	±0.05
A2	1.14	1.14	±0.15
b	0.40	0.40	±0.05
c	0.14	0.14	±0.06
D	2.90	2.90	Basic
E	2.80	2.80	Basic
E1	1.60	1.60	Basic
e	0.95	0.95	Basic
e1	1.90	1.90	Basic
L	0.45	0.45	±0.10
L1	0.60	0.60	Reference
N	5	6	Reference

Rev. F 2/07

NOTES:

1. Plastic or metal protrusions of 0.25mm maximum per side are not included.

2. Plastic interlead protrusions of 0.25mm maximum per side are not included.

3. This dimension is measured at Datum Plane "H".

4. Dimensioning and tolerancing per ASME Y14.5M-1994.

5. Index area - Pin #1 I.D. will be located within the indicated zone (SOT23-6 only).

6. SOT23-5 version has no center lead (shown as a dashed line).

Small Outline Transistor Plastic Packages (SC70-5)
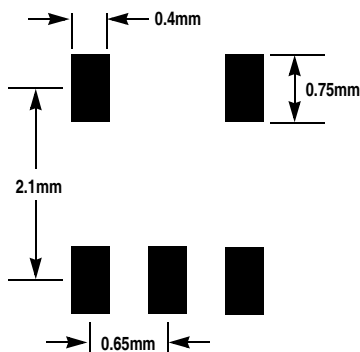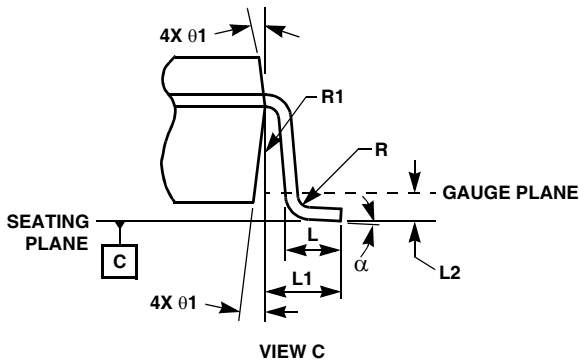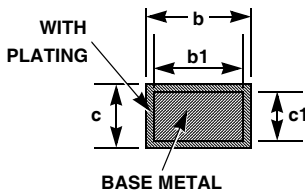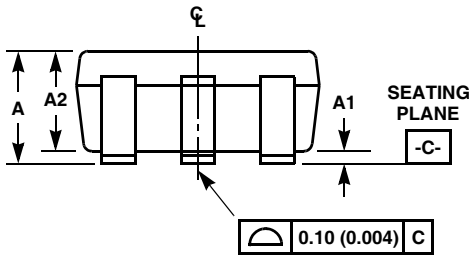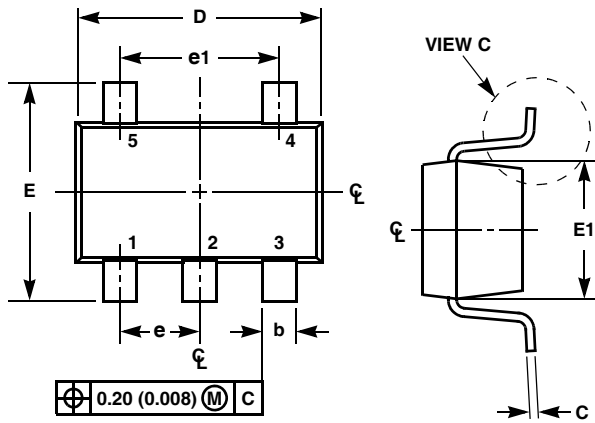
P5.049
5 LEAD SMALL OUTLINE TRANSISTOR PLASTIC PACKAGE

| SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.031	0.043	0.80	1.10	-
A1	0.000	0.004	0.00	0.10	-
A2	0.031	0.039	0.80	1.00	-
b	0.006	0.012	0.15	0.30	-
b1	0.006	0.010	0.15	0.25	
c	0.003	0.009	0.08	0.22	6
c1	0.003	0.009	0.08	0.20	6
D	0.073	0.085	1.85	2.15	3
E	0.071	0.094	1.80	2.40	-
E1	0.045	0.053	1.15	1.35	3
e	0.0256 Ref		0.65 Ref		-
e1	0.0512 Ref		1.30 Ref		-
L	0.010	0.018	0.26	0.46	4
L1	0.017 Ref.		0.420 Ref.		-
L2	0.006 BSC		0.15 BSC		
α	0°	8°	0°	8°	-
N	5		5		5
R	0.004	-	0.10	-	
R1	0.004	0.010	0.15	0.25	

Rev. 3 7/07

NOTES:

1. Dimensioning and tolerances per ASME Y14.5M-1994.

2. Package conforms to EIAJ SC70 and JEDEC MO-203AA.

3. Dimensions D and E1 are exclusive of mold flash, protrusions, or gate burrs.

4. Footlength L measured at reference to gauge plane.

5. "N" is the number of terminal positions.

6. These Dimensions apply to the flat section of the lead between 0.08mm and 0.15mm from the lead tip.

7. Controlling dimension: MILLIMETER. Converted inch dimensions are for reference only.

TYPICAL RECOMMENDED LAND PATTERN

Package Outline Drawing

L6.1.6x1.6

6 LEAD ULTRA THIN DUAL FLAT NO-LEAD COL PLASTIC PACKAGE (UTDFN COL)

Rev 1, 11/07

TOP VIEW

BOTTOM VIEW

TYPICAL RECOMMENDED LAND PATTERN

SIDE VIEW

DETAIL "X"
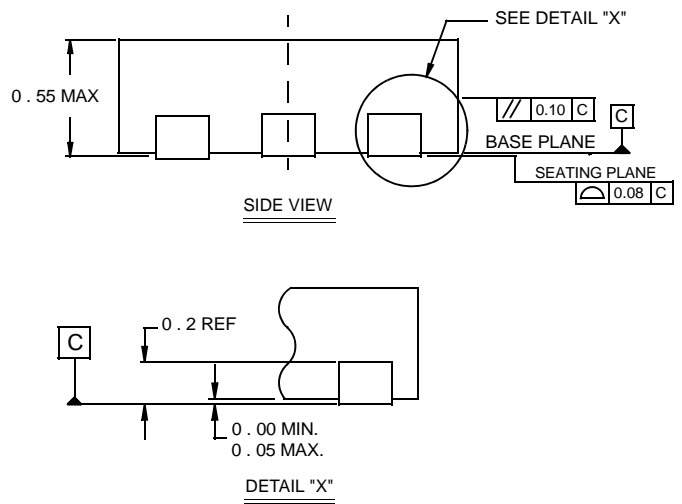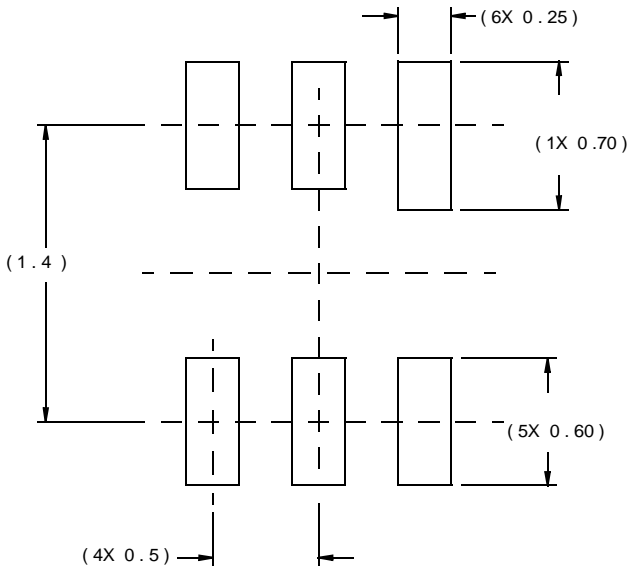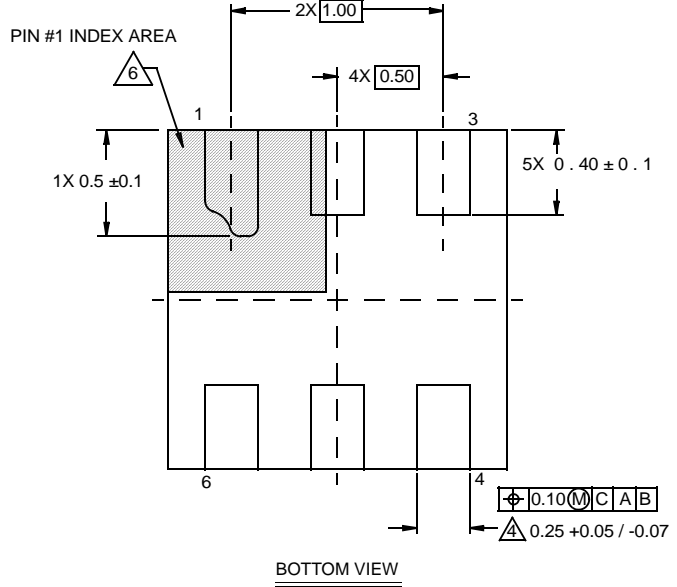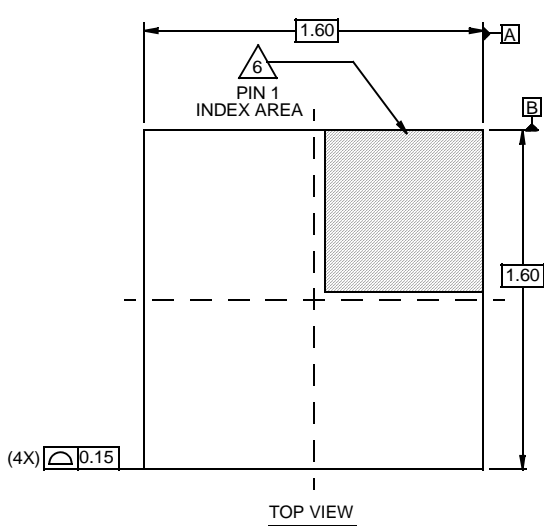
NOTES:

1. Dimensions are in millimeters.
   Dimensions in ( ) for Reference Only.

2. Dimensioning and tolerancing conform to AMSE Y14.5m-1994.

3. Unless otherwise specified, tolerance : Decimal ± 0.05

4. Dimension b applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.

5. Tiebar shown (if present) is a non-functional feature.

6. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.

Mini SO Package Family (MSOP)
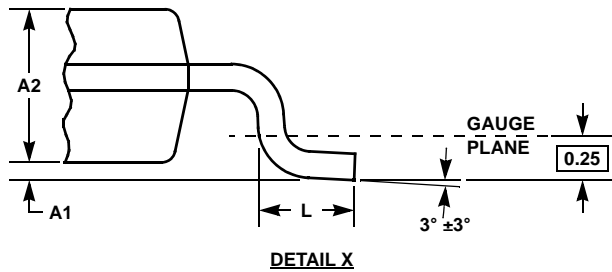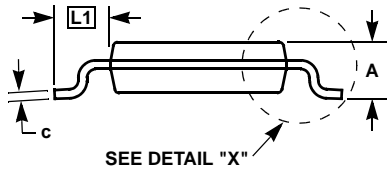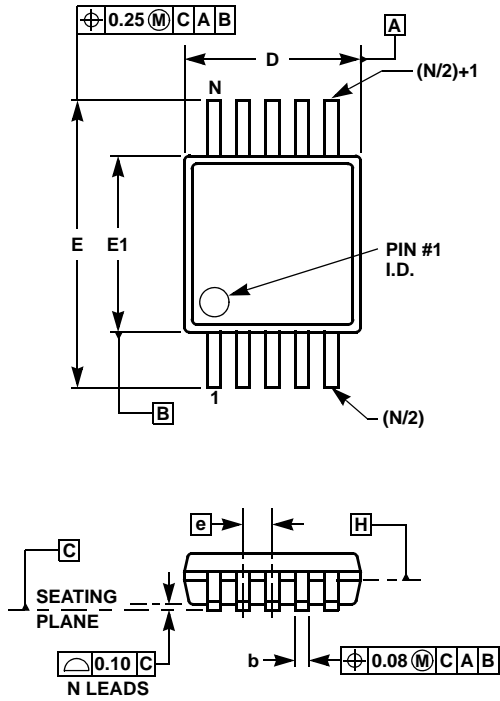

MDP0043

MINI SO PACKAGE FAMILY

| SYMBOL | MILLIMETERS | | TOLERANCE | NOTES |
	MSOP8	MSOP10		
A	1.10	1.10	Max.	-
A1	0.10	0.10	±0.05	-
A2	0.86	0.86	±0.09	-
b	0.33	0.23	+0.07/-0.08	-
c	0.18	0.18	±0.05	-
D	3.00	3.00	±0.10	1, 3
E	4.90	4.90	±0.15	-
E1	3.00	3.00	±0.10	2, 3
e	0.65	0.50	Basic	-
L	0.55	0.55	±0.15	-
L1	0.95	0.95	Basic	-
N	8	10	Reference	-

Rev. D 2/07

NOTES:

1. Plastic or metal protrusions of 0.15mm maximum per side are not included.

2. Plastic interlead protrusions of 0.25mm maximum per side are not included.

3. Dimensions "D" and "E1" are measured at Datum Plane "H".

4. Dimensioning and tolerancing per ASME Y14.5M-1994.

Thin Shrink Small Outline Plastic Packages (TSSOP)
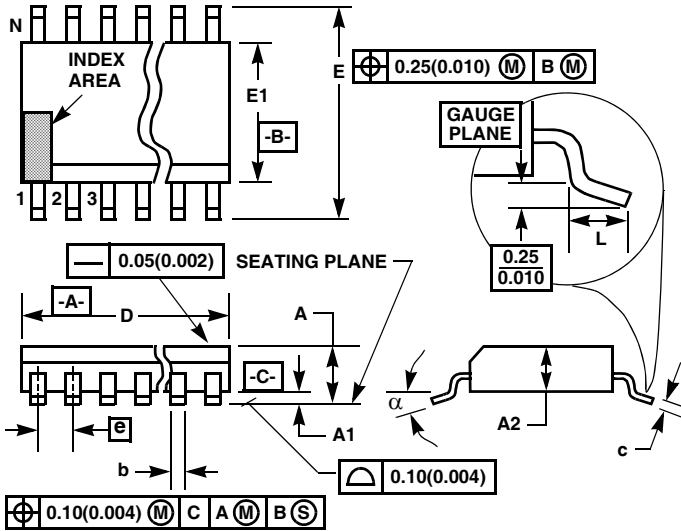
M14.173

14 LEAD THIN SHRINK SMALL OUTLINE PLASTIC PACKAGE

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	-	0.047	-	1.20	-
A1	0.002	0.006	0.05	0.15	-
A2	0.031	0.041	0.80	1.05	-
b	0.0075	0.0118	0.19	0.30	9
c	0.0035	0.0079	0.09	0.20	-
D	0.195	0.199	4.95	5.05	3
E1	0.169	0.177	4.30	4.50	4
e	0.026 BSC		0.65 BSC		-
E	0.246	0.256	6.25	6.50	-
L	0.0177	0.0295	0.45	0.75	6
N	14		14		7
α	0°	8°	0°	8°	-

Rev. 2 4/06

NOTES:

1. These package dimensions are within allowable dimensions of JEDEC MO-153-AC, Issue E.

2. Dimensioning and tolerancing per ANSI Y14.5M-1982.

3. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.

4. Dimension "E1" does not include interlead flash or protrusions. Inter-lead flash and protrusions shall not exceed 0.15mm (0.006 inch) per side.

5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.

6. "L" is the length of terminal for soldering to a substrate.

7. "N" is the number of terminal positions.

8. Terminal numbers are shown for reference only.

9. Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall be 0.08mm (0.003 inch) total in excess of "b" dimension at maximum material condition. Minimum space between protrusion and adjacent lead is 0.07mm (0.0027 inch).

10. Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact. (Angles in degrees)

FN6560.1
May 29, 2009